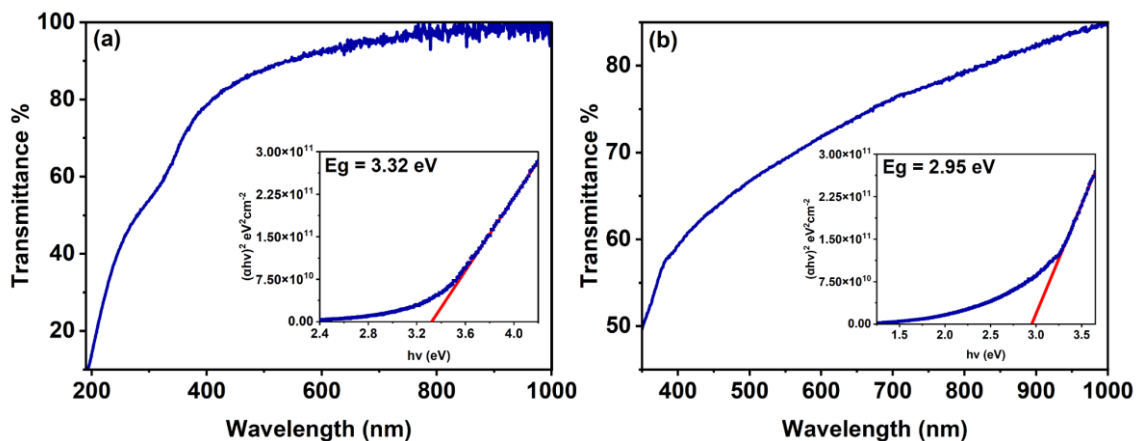
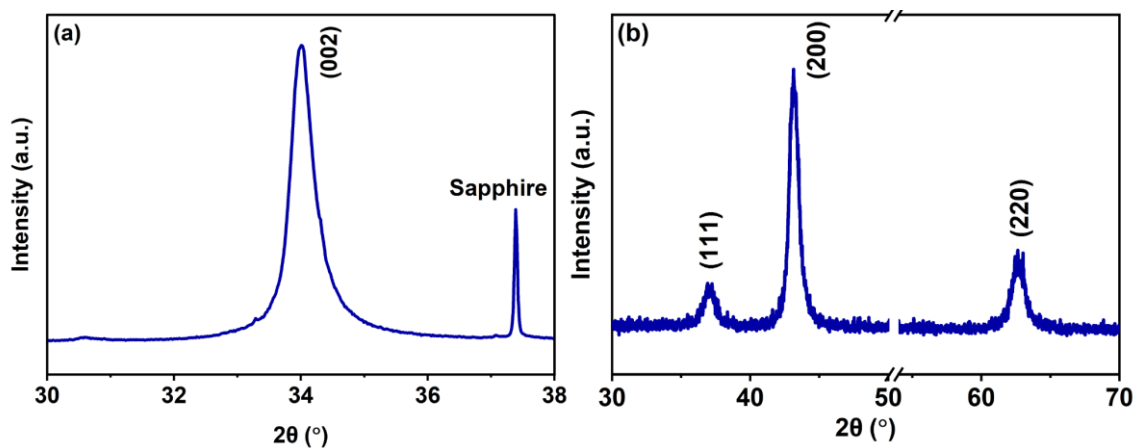


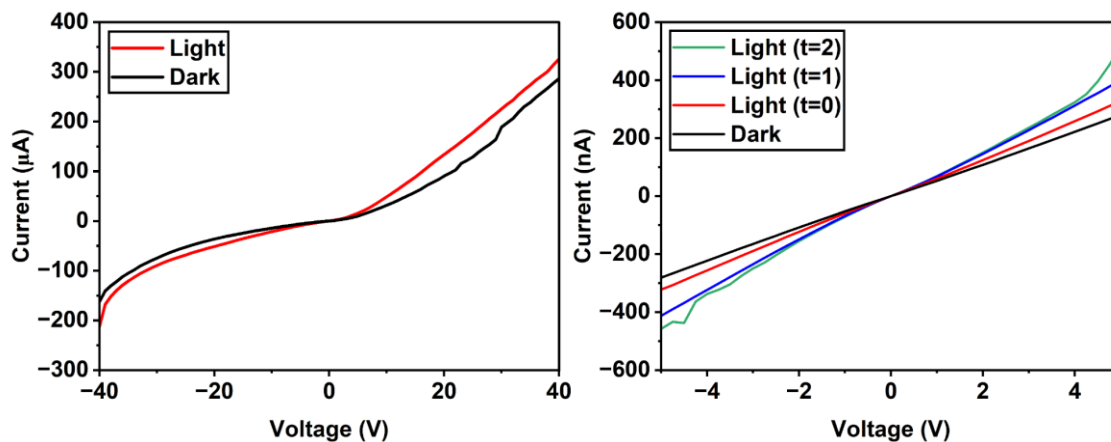
## GaN and NiO Metal-Semiconductor-Metal Photodetectors Fabricated via Hollow-Cathode Plasma-Assisted Atomic Layer Deposition



**Figure 1.** Transmittance spectra for (a) GaN film deposited on sapphire and (b) NiO film deposited on glass substrates. Insets show Tauc plots and calculated bandgap energy values.



**Figure 2.** XRD patterns for (a) GaN film deposited on sapphire and (b) NiO film deposited on glass.



**Figure 3.** MSM PD I-V characteristics in dark and illuminated conditions. (a) GaN on sapphire and (b) NiO on glass.